

CMOS

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Group 6

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Introduction and physical properties

1- Cell Description

This cell consists of a CMOS inverter. They are extremely common and one of the most used circuitry. Cmos inverters are used in every digital device that exists. It takes whatever the input may be ,and it inverts it. For example, if the input is a logic 1, the inverter will take that input and transform it into a logic 0.

2- Cell Symbols

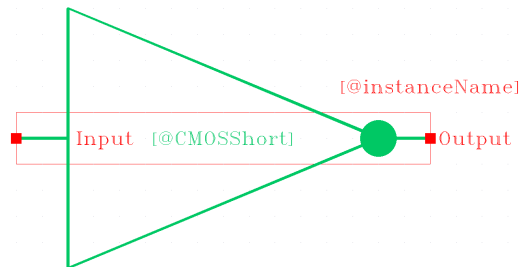


Figure 1: CMOS inverter (normal)

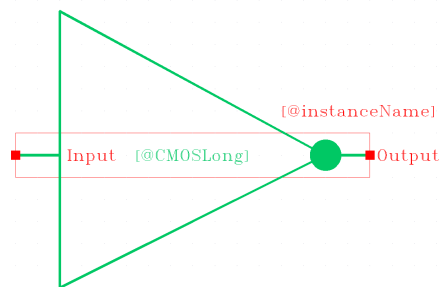


Figure 2: CMOS inverter (long)

3- Cell Truth Table (for both cmos inverters)

Cell input	Cell output
A	Y
0	1
1	0

4- Cell schematic

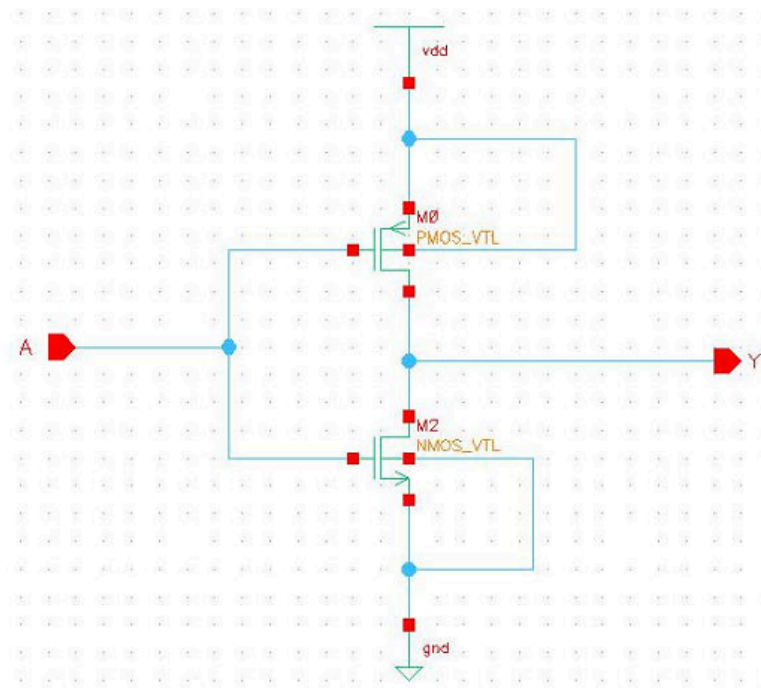


Figure 3: CMOS inverter (short)

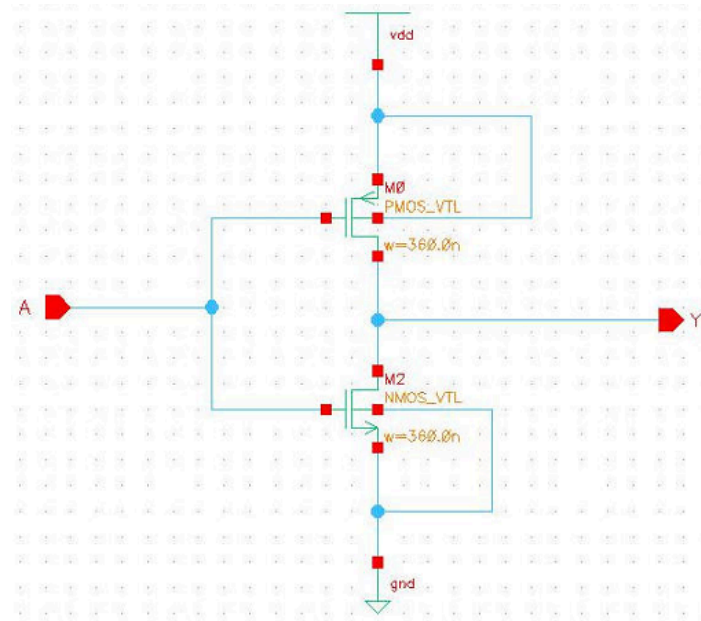


Figure 4: CMOS inverter (long)

5- Cell Dimensions

CMOS

transistor instance number	Width (nm)	Length (nm)
PMOS (M0)	90	50
NMOS (M2)	90	50

CMOS Long

transistor instance number	Width (nm)	Length (nm)
PMOS(M0)	360	50
NMOS(M2)	360	50

6- Input X: output rise time data**CMOS**

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	391.1	-----

CMOS Long

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	94.56	-----

7- Input X: output fall time data**CMOS**

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	116.6	-----

CMOS Long

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	32.14	-----

8- Data worst case Low to High propagation delay t_{plh} **CMOS**

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	275.404	-----

CMOS Long

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	75.756	-----

9- Data worst case High to Low propagation delay t_{phl} **CMOS**

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	96.995	-----

CMOS Long

Input rise/fall time (ps)	FO0	FO1	FO2	FO4	FO8
40	-----	-----	-----	31.985	-----

10- Transient analysis

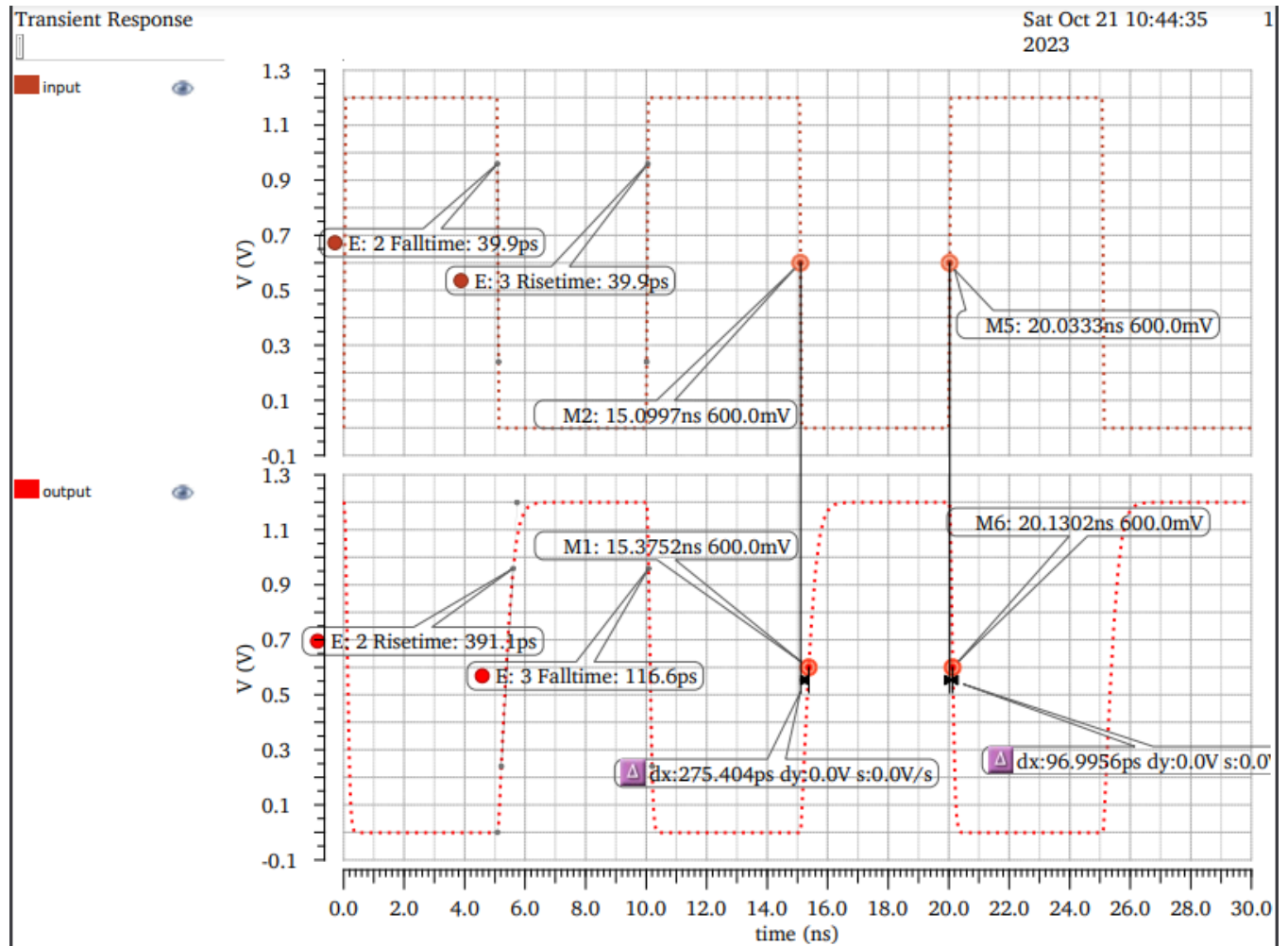


Figure 5: Transient analysis on the normal CMOS circuitry

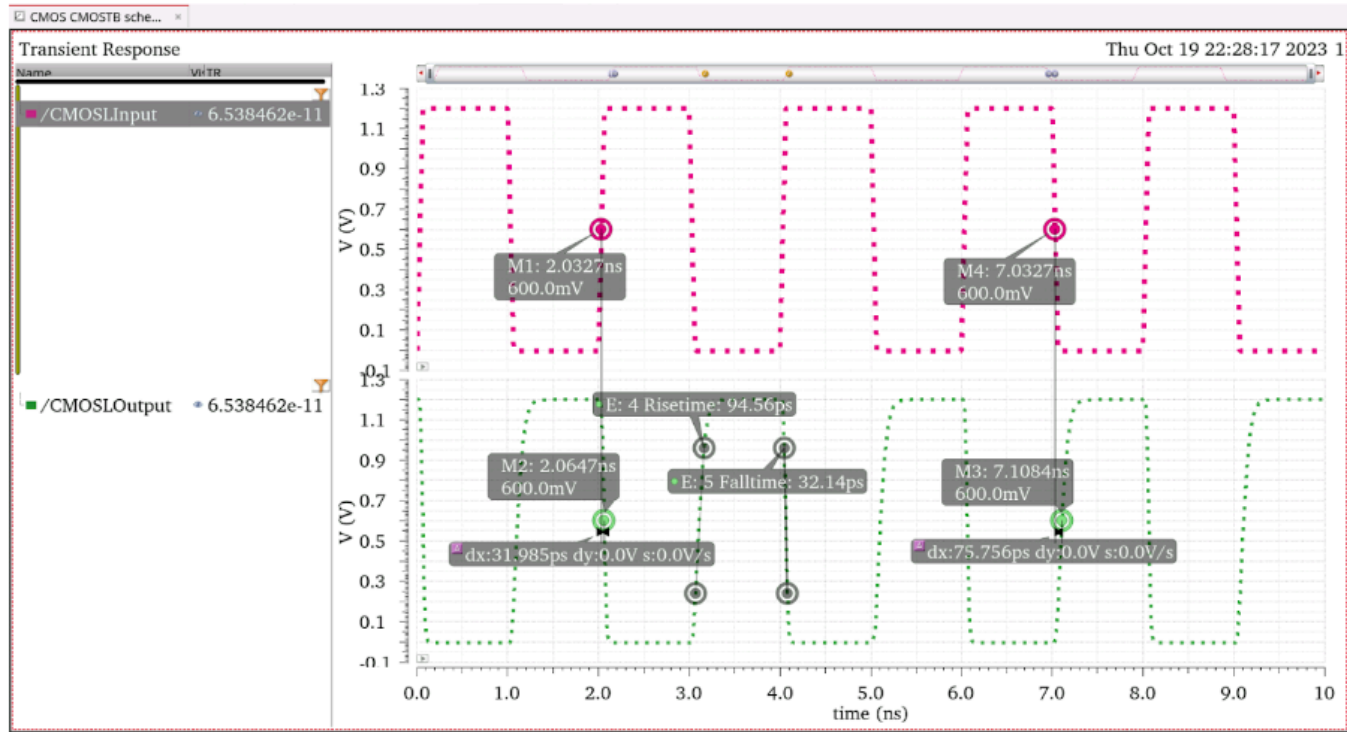


Figure 6: Transient analysis on the CMOS Long circuitry

Table 1: Transient analysis table

TYPE	t_{plh} (ps)	t_{phl} (ps)	t_r (ps)	t_f (ps)
CMOS	275.404	96.995	391.1	116.6
CMOS_LONG	75.756	31.985	94.56	32.14
Enhancement mode NFET	323.892	72.1549	1560	74.74
Enhancement mode NFET Long	1034.43	62.3649	4724	77.4
Resistive load	590.613	100.105	880.5	118.2
Resistive load Long	2082.7	90.7394	2925	105.8

11- DC analysis

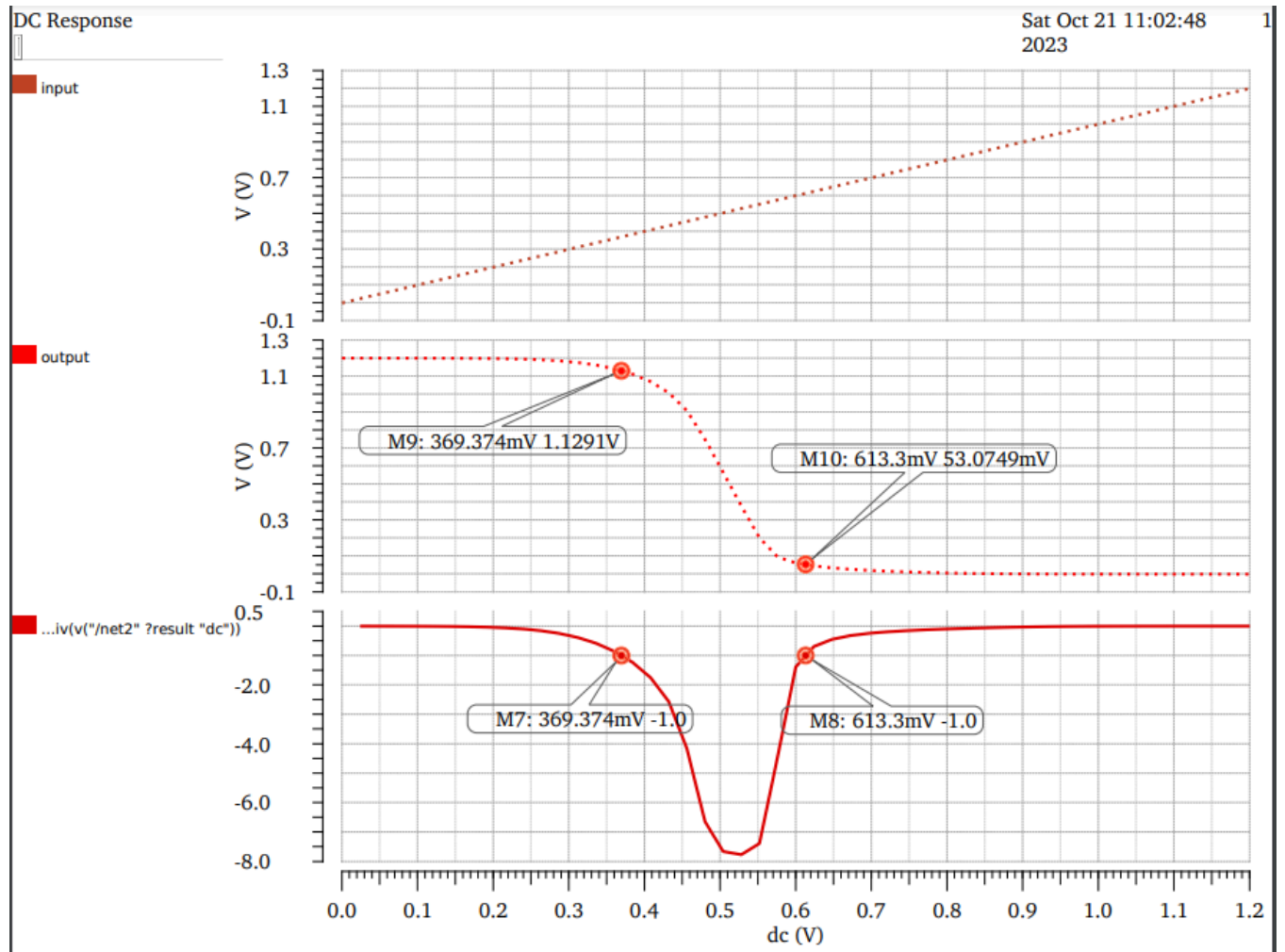


Figure 7: DC analysis on the normal CMOS circuitry

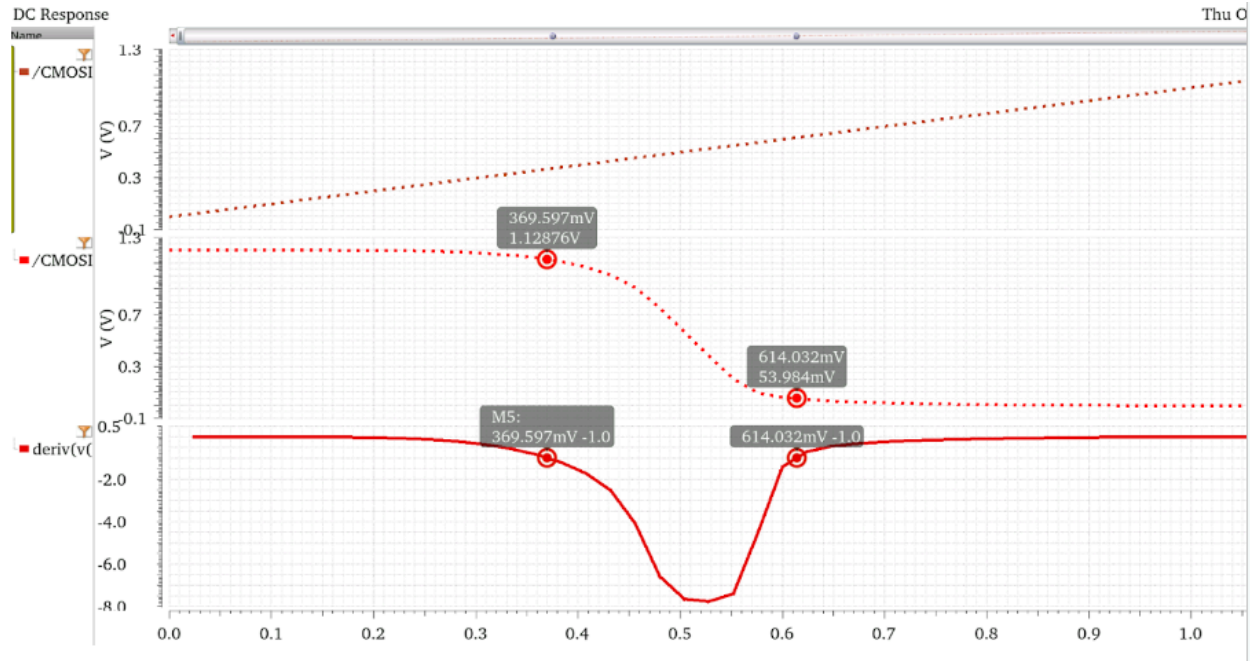


Figure 8: DC analysis on the CMOS Long circuitry

Table 2: DC Analysis table

TYPE	V_{IH_DC} (mV)	V_{IL_DC} (mV)	V_{OH_DC} (mV)	V_{OL_DC} (mV)
CMOS	613.3	369.374	1129.1	53.0749
CMOS_LONG	614.032	369.597	1128.76	53.984
Enhancement mode NFET	344.75	624.697	508.485	117.365
Enhancement mode NFET Long	270.272	550.588	528.809	66.047
Resistive load	677.123	307.049	1126.49	115.919
Resistive load Long	558.172	239.854	1132.73	56.047